

描述 / Descriptions

TO-252 塑封封装 N 沟道 MOS 场效应管。N-CHANNEL MOSFET in a TO-252 Plastic Package.

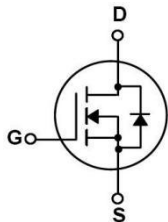
特征 / Features

低栅电荷,低反馈电容,开关速度快。
Low gate charge, low crss, fast switching.

用途 / Applications

用于高功率 DC/DC 转换和功率开关。
These devices are well suited for high efficiency switching DC/DC converters and switch mode power supplies.

内部等效电路 / Equivalent Circuit



引脚排列 / Pinning



PIN1: G PIN 2: D PIN 3: S PIN 4: D

放大及印章代码 / h_{FE} Classifications & Marking

见印章说明。 See Marking Instructions

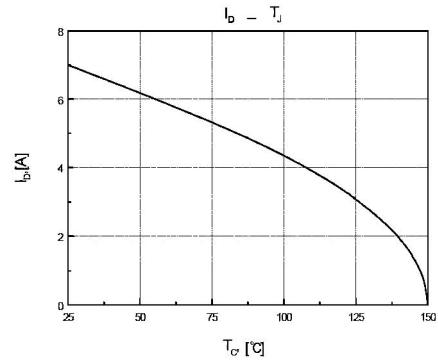
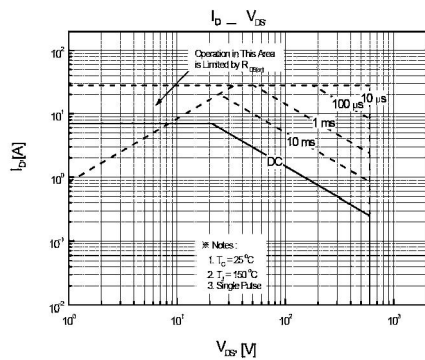
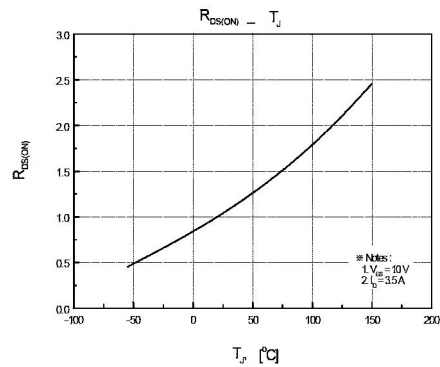
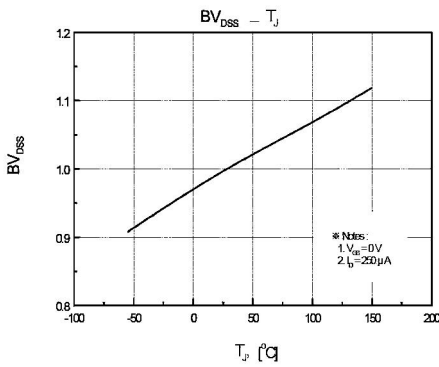
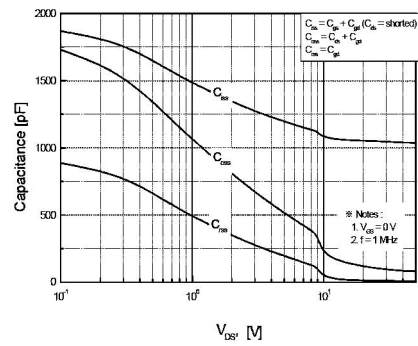
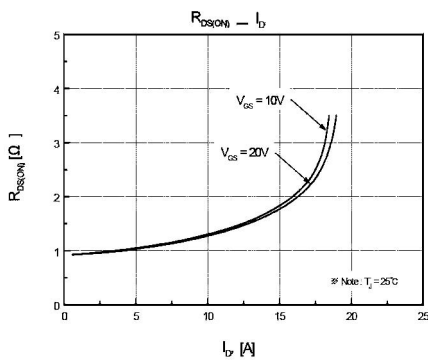
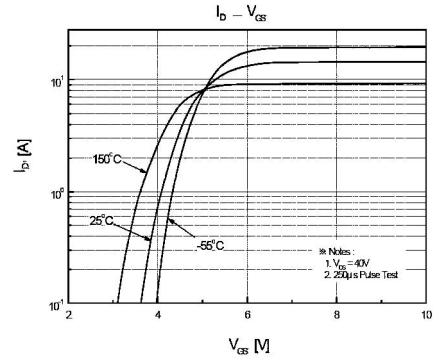
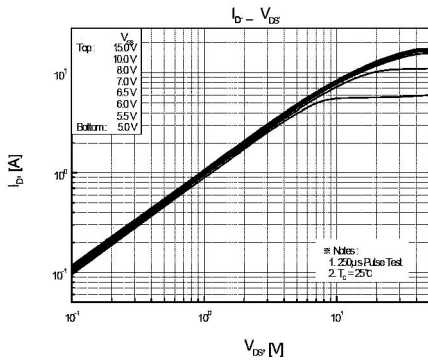
极限参数 / Absolute Maximum Ratings(Ta=25°C)

参数 Parameter	符号 Symbol	数值 Rating	单位 Unit
Drain-Source Voltage	V_{DSS}	650	V
Drain Current	$I_D(T_C=25^\circ C)$	7.0	A
Drain Current	$I_D(T_C=100^\circ C)$	4.4	A
Drain Current - Pulsed	I_{DM}	28	A
Gate-Source Voltage	V_{GSS}	± 30	V
Single Pulsed Avalanche Energy	E_{AS}	420	mJ
Repetitive Avalanche Energy	E_{AR}	14.7	mJ
Avalanche Current	I_{AR}	7.0	A
Power Dissipation	$P_D(T_C=25^\circ C)$	95	W
Operating and Storage Temperature Range	T_j, T_{stg}	-55 to 150	$^\circ C$

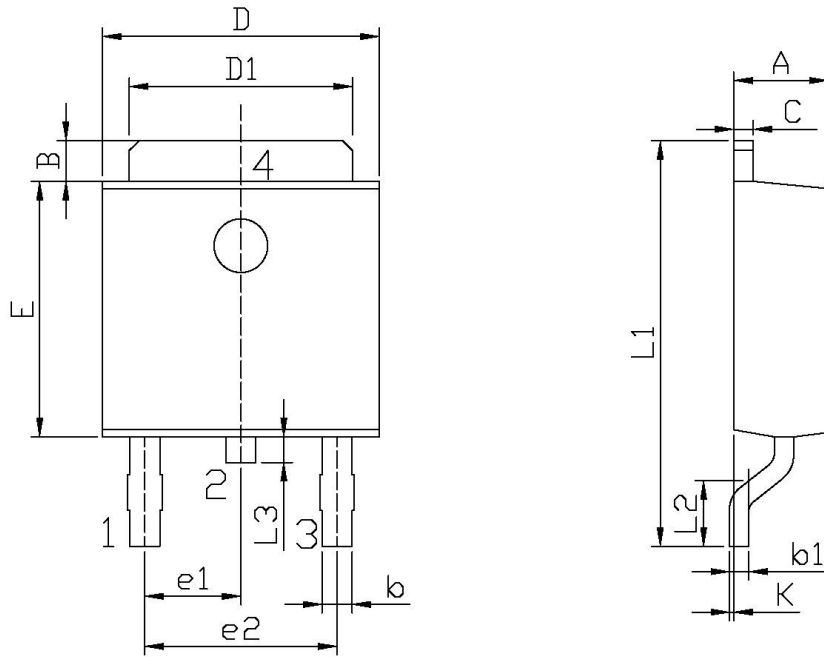
电性能参数 / Electrical Characteristics(Ta=25°C)

参数 Parameter	符号 Symbol	测试条件 Test Conditions	最小值 Min	典型值 Typ	最大值 Max	单位 Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V$ $I_D=250\mu A$	650			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=650V$ $V_{GS}=0V$			1.0	μA
		$V_{DS}=520V$ $T_C=125^\circ C$			100	μA
Gate-Body Leakage Current, Forward	I_{GSS}	$V_{GS}=\pm 30V$ $V_{DS}=0V$			± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ $I_D=250\mu A$	2.0		4.0	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10V$ $I_D=3.5A$			1.5	Ω
Forward Transconductance	g_{FS}	$V_{DS}=40V$ $I_D=3.5A$		8.2		S
Drain-Source Diode Forward Voltage	V_{SD}	$V_{GS}=0V$ $I_S=7.0A$			1.4	V
Input Capacitance	C_{iss}	$V_{DS}=25V$ $V_{GS}=0V$ $f=1.0MHz$		1100	1500	pF
Output Capacitance	C_{oss}			110	150	pF
Reverse Transfer Capacitance	C_{rss}			12	16	pF
Turn-On Delay Time	$t_{d(on)}$	$V_{DD}=300V$ $I_D=7.0A$ $R_G=25\Omega$		15	40	ns
Turn-On Rise Time	t_r			30	70	ns
Turn-Off Delay Time	$t_{d(off)}$			110	230	ns
Turn-Off Fall Time	t_f			40	90	ns

电参数曲线图 / Electrical Characteristic Curve



外形尺寸图 / Package Dimensions

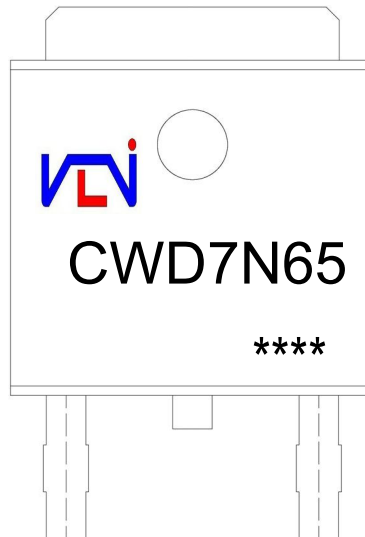


单位: mm

Symbol	Dimensions In Millimeters		Symbol	Dimensions In Millimeters	
	Min	Max		Min	Max
A	2.20	2.40	E	5.95	6.25
B	0.95	1.25	e1	2.24	2.34
b	0.50	0.70	e2	4.43	4.73
b1	0.45	0.55	L1	9.45	9.95
C	0.45	0.55	L2	1.25	1.75
D	6.45	6.75	L3	0.60	0.90
D1	5.10	5.50	K	0.00	0.10

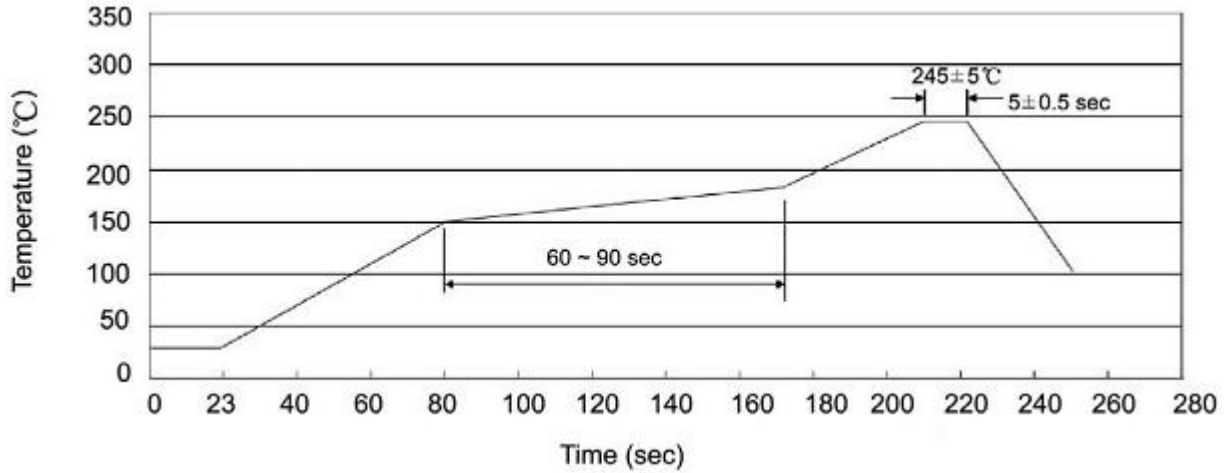
TO-252

印章说明 / Marking Instructions



- 说明:
- CWD: 为公司代码
- 7N65: 为型号代码
- ****: 为生产批号代码, 随生产批号变化。
- Note:
- CWD: Company Code
- 7N65: Product Type
- ****: Lot No. Code, code change with Lot No.

回流焊温度曲线图(无铅) / Temperature Profile for IR Reflow Soldering(Pb-Free)



说明:

1. 预热温度 25~150°C, 时间 60~90sec;
2. 峰值温度 245±5°C, 时间持续为 5±0.5sec;
3. 焊接制程冷却速度为 2~10°C/sec.

Note:

1. Preheating: 25~150°C, Time: 60~90sec.
2. Peak Temp.: 245±5°C, Duration: 5±0.5sec.
3. Cooling Speed: 2~10°C/sec.

耐焊接热试验条件 / Resistance to Soldering Heat Test Conditions

温度: 260±5°C

时间: 10±1 sec.

Temp.: 260±5°C

Time: 10±1 sec

包装规格 / Packaging SPEC.

卷盘包装 / REEL

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	Units/Reel 只/卷盘	Reels/Inner Box 卷盘/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Reel	Inner Box 盒	Outer Box 箱
TO-252	2,500	2	5,000	5	25,000	13" ×16	360×360×50	385×257×392

套管包装 / TUBE

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	Units/Tube 只/套管	Tubes/Inner Box 套管/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Tube 套管	Inner Box 盒	Outer Box 箱
TO-251/252	75	48	3,600	5	18,000	526×20.5×5.25	555×164×50	575×290×180

使用说明 / Notices